

## **Erratum: Designing a Hetrostructure Junctionless-Field Effect Transistor (HJL-FET) for High-speed Applications**

[J. Korean Phys. Soc. **71**, 275 (2017)]  
DOI: 10.3938/jkps.71.275

Mahdi VADIZADEH\*

*Department of Electrical Engineering, Abhar Branch, Islamic Azad University, Abhar, Iran*

DOI: 10.3938/jkps.72.645

The submitted date of this paper should be corrected. It should be written as “Received 20 March 2017, in final form 13 July 2017” instead of “Received 25 May 2017, in final form 13 July 2017”.

---

\*E-mail: Vadizadeh@gmail.com